



NX7002AKW

60 V, single N-channel Trench MOSFET

Rev. 1 — 1 March 2012

Product data sheet

1. Product profile

1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT323 (SC-70) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Very fast switching
- Trench MOSFET technology
- ESD protected

1.3 Applications

- Relay driver
- High-speed line driver
- Low-side load switch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

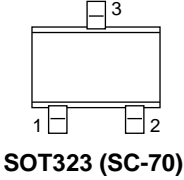
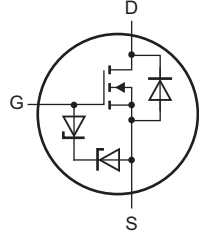
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j = 25\text{ °C}$	-	-	60	V
V_{GS}	gate-source voltage		-20	-	20	V
I_D	drain current	$V_{GS} = 10\text{ V}; T_{amb} = 25\text{ °C}$	[1]	-	170	mA
Static characteristics						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 100\text{ mA}; T_j = 25\text{ °C}$	-	3	4.5	Ω

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 <p>SOT323 (SC-70)</p>	 <p>017aaa255</p>
2	S	source		
3	D	drain		

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
NX7002AKW	SC-70	plastic surface-mounted package; 3 leads	SOT323

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
NX7002AKW	AH%

[1] % = placeholder for manufacturing site code

5. Limiting values

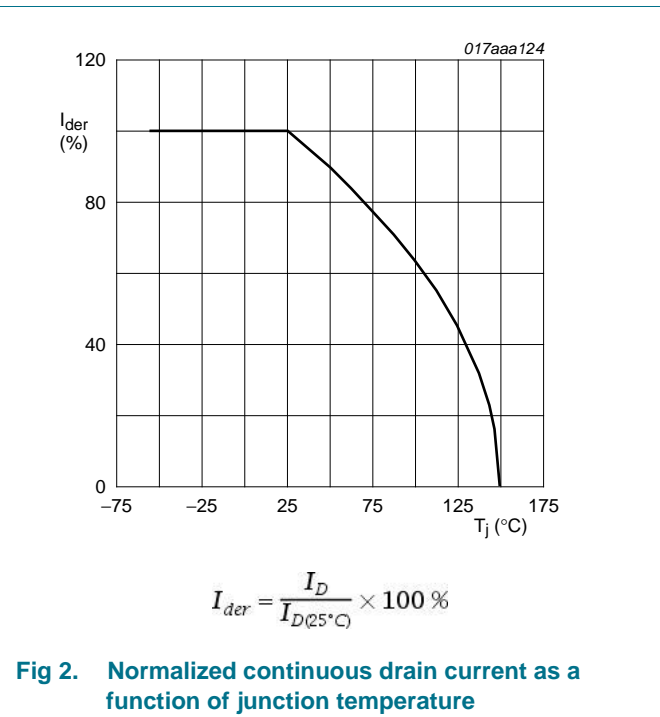
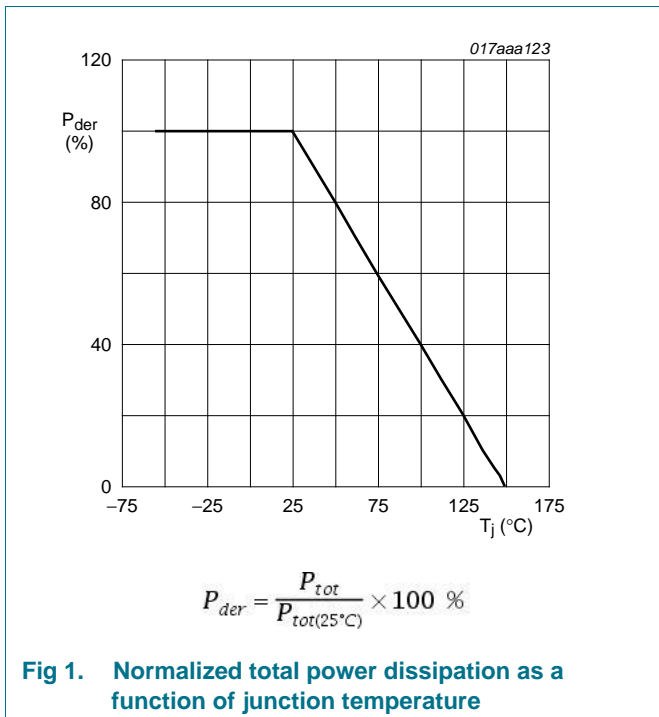
Table 5. Limiting values

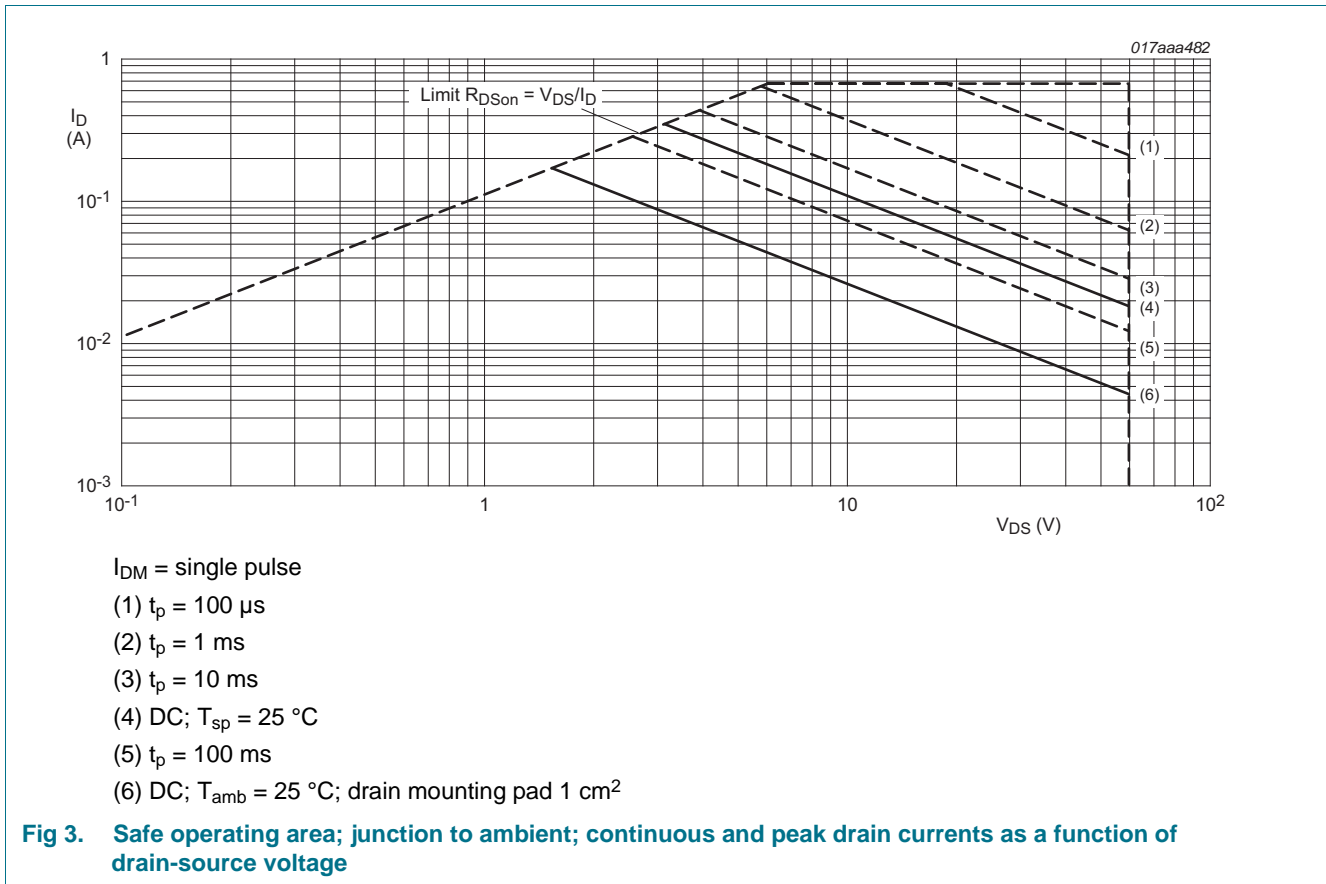
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
V _{DS}	drain-source voltage	T _j = 25 °C	-	60	V	
V _{GS}	gate-source voltage		-20	20	V	
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	170	mA
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	100	mA
I _{DM}	peak drain current	T _{amb} = 25 °C; single pulse; t _p ≤ 10 μs	-	680	mA	
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	220	mW
			[1]	-	255	mW
		T _{sp} = 25 °C		-	1060	mW
T _j	junction temperature		-55	150	°C	
T _{amb}	ambient temperature		-55	150	°C	
T _{stg}	storage temperature		-65	150	°C	
Source-drain diode						
I _S	source current	T _{amb} = 25 °C	[1]	-	170	mA

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.





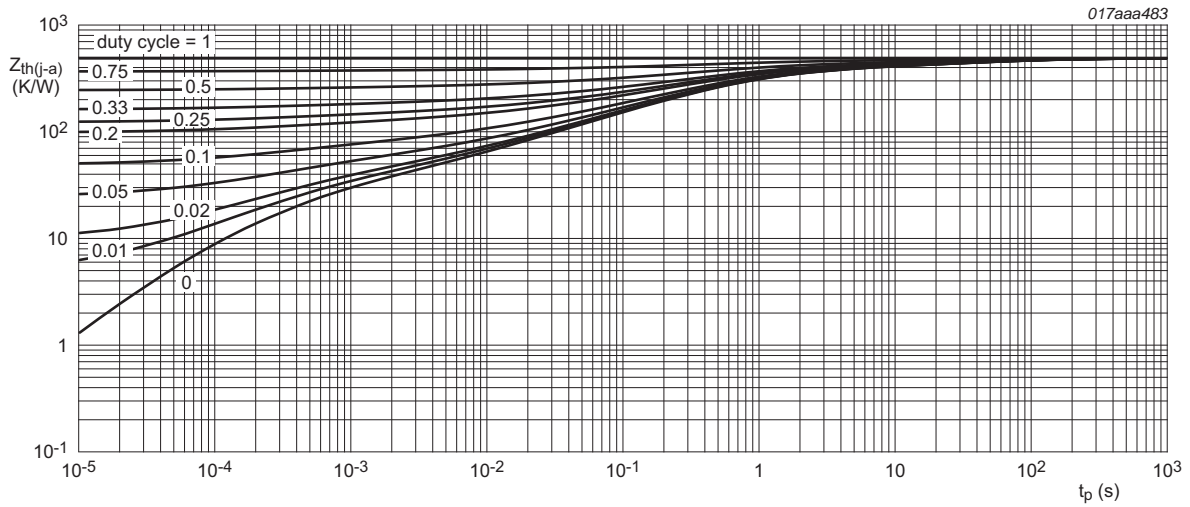
6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	[1]	-	485	560	K/W
		[2]	-	420	480	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	115	K/W

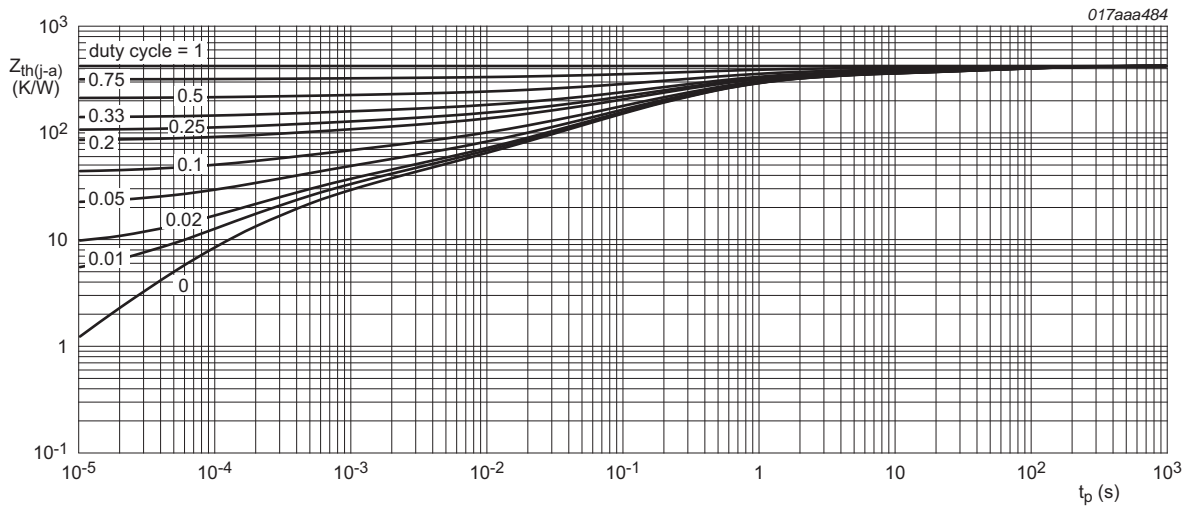
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm^2 .



FR4 PCB, standard footprint

Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



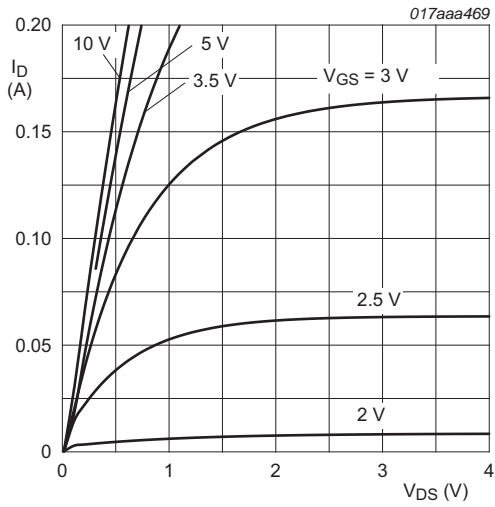
FR4 PCB, mounting pad for drain 1 cm²

Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

7. Characteristics

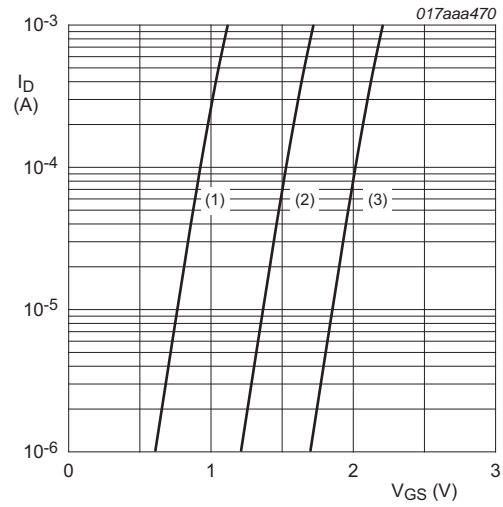
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A$; $V_{GS} = 0 V$; $T_j = 25 \text{ }^\circ\text{C}$	60	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A$; $V_{DS} = V_{GS}$; $T_j = 25 \text{ }^\circ\text{C}$	1.1	1.6	2.1	V
I_{DSS}	drain leakage current	$V_{DS} = 60 V$; $V_{GS} = 0 V$; $T_j = 25 \text{ }^\circ\text{C}$	-	-	1	μA
		$V_{DS} = 60 V$; $V_{GS} = 0 V$; $T_j = 150 \text{ }^\circ\text{C}$	-	-	10	μA
I_{GSS}	gate leakage current	$V_{GS} = 20 V$; $V_{DS} = 0 V$; $T_j = 25 \text{ }^\circ\text{C}$	-	-	2	μA
		$V_{GS} = -20 V$; $V_{DS} = 0 V$; $T_j = 25 \text{ }^\circ\text{C}$	-	-	2	μA
		$V_{GS} = 10 V$; $V_{DS} = 0 V$; $T_j = 25 \text{ }^\circ\text{C}$	-	-	0.5	μA
		$V_{GS} = -10 V$; $V_{DS} = 0 V$; $T_j = 25 \text{ }^\circ\text{C}$	-	-	0.5	μA
		$V_{GS} = 5 V$; $V_{DS} = 0 V$; $T_j = 25 \text{ }^\circ\text{C}$	-	-	100	μA
		$V_{GS} = -5 V$; $V_{DS} = 0 V$; $T_j = 25 \text{ }^\circ\text{C}$	-	-	100	μA
R_{DSon}	drain-source on-state resistance	$V_{GS} = 10 V$; $I_D = 100 \text{ mA}$; $T_j = 25 \text{ }^\circ\text{C}$	-	3	4.5	Ω
		$V_{GS} = 10 V$; $I_D = 100 \text{ mA}$; $T_j = 150 \text{ }^\circ\text{C}$	-	6.2	9.2	Ω
		$V_{GS} = 5 V$; $I_D = 100 \text{ mA}$; $T_j = 25 \text{ }^\circ\text{C}$	-	3.7	5.2	Ω
g_{fs}	forward transconductance	$V_{DS} = 10 V$; $I_D = 200 \text{ mA}$; $T_j = 25 \text{ }^\circ\text{C}$	-	230	-	mS
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$V_{DS} = 30 V$; $I_D = 200 \text{ mA}$; $V_{GS} = 4.5 V$; $T_j = 25 \text{ }^\circ\text{C}$	-	0.33	0.43	nC
Q_{GS}	gate-source charge		-	0.12	-	nC
Q_{GD}	gate-drain charge		-	0.09	-	nC
C_{iss}	input capacitance	$V_{DS} = 10 V$; $f = 1 \text{ MHz}$; $V_{GS} = 0 V$; $T_j = 25 \text{ }^\circ\text{C}$	-	11	17	pF
C_{oss}	output capacitance		-	3.4	-	pF
C_{rss}	reverse transfer capacitance		-	1.4	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 40 V$; $R_L = 250 \Omega$; $V_{GS} = 10 V$; $R_{G(ext)} = 6 \Omega$; $T_j = 25 \text{ }^\circ\text{C}$	-	6	12	ns
t_r	rise time		-	7	-	ns
$t_{d(off)}$	turn-off delay time		-	20	40	ns
t_f	fall time		-	14	-	ns
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 115 \text{ mA}$; $V_{GS} = 0 V$; $T_j = 25 \text{ }^\circ\text{C}$	0.47	0.7	1.2	V



$T_j = 25\text{ }^\circ\text{C}$

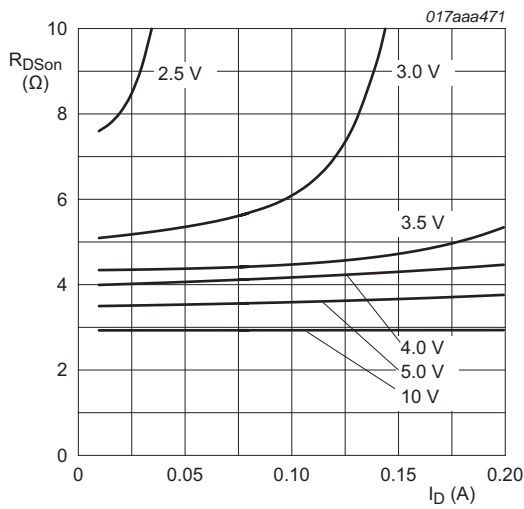
Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values



$T_j = 25\text{ }^\circ\text{C}; V_{DS} = 5\text{ V}$

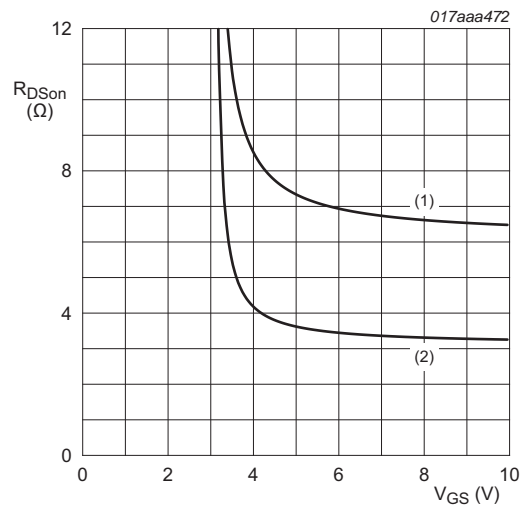
- (1) minimum values
- (2) typical values
- (3) maximum values

Fig 7. Subthreshold drain current as a function of gate-source voltage



$T_j = 25\text{ }^\circ\text{C}$

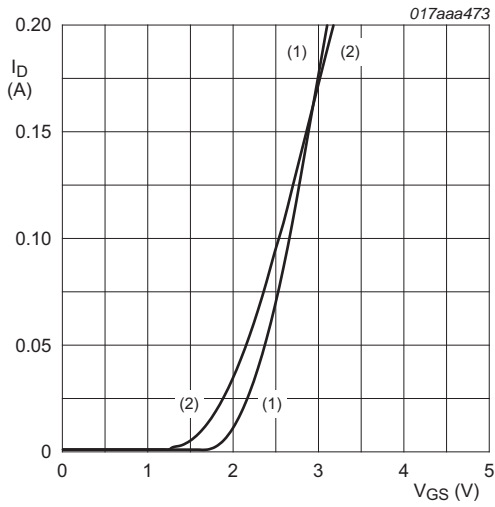
Fig 8. Drain-source on-state resistance as a function of drain current; typical values



$I_D = 0.2\text{ A}$

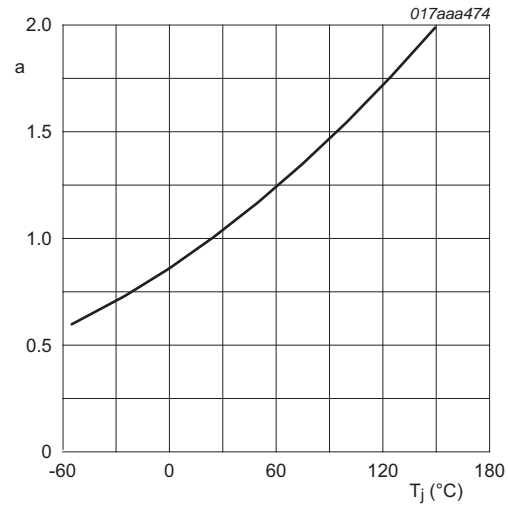
- (1) $T_j = 150\text{ }^\circ\text{C}$
- (2) $T_j = 25\text{ }^\circ\text{C}$

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values



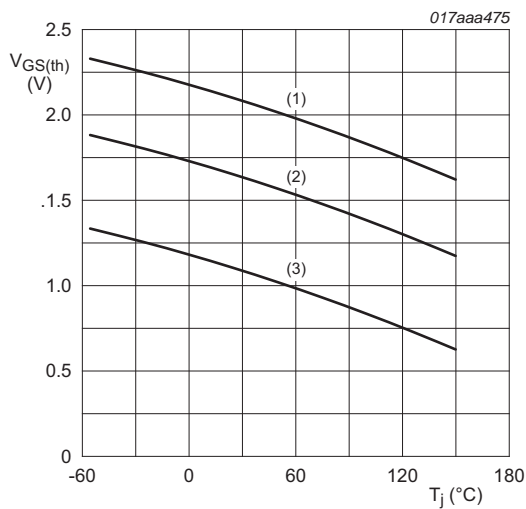
$V_{DS} > I_D \times R_{DS(on)}$
 (1) $T_j = 25\text{ °C}$
 (2) $T_j = 150\text{ °C}$

Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



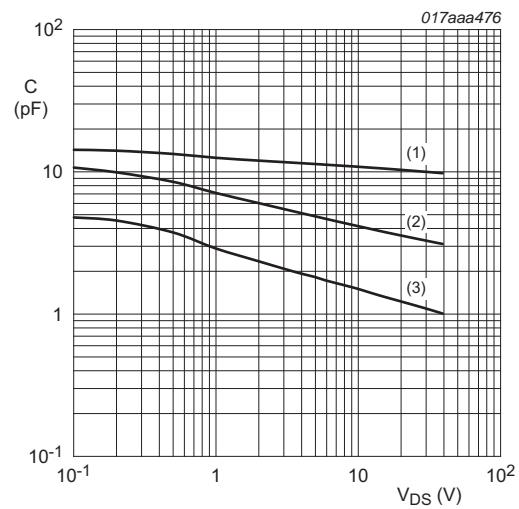
$$a = \frac{R_{DS(on)}}{R_{DS(on)}(25\text{°C})}$$

Fig 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values



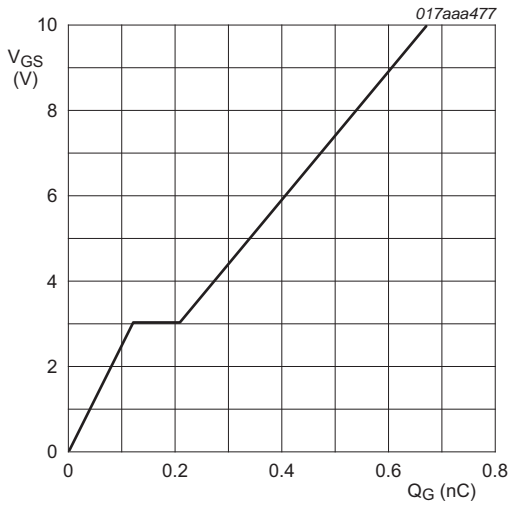
$I_D = 0.25\text{ mA}; V_{DS} = V_{GS}$
 (1) maximum values
 (2) typical values
 (3) minimum values

Fig 12. Gate-source threshold voltage as a function of junction temperature



$f = 1\text{ MHz}; V_{GS} = 0\text{ V}$
 (1) C_{iss}
 (2) C_{oss}
 (3) C_{rss}

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$I_D = 0.2 \text{ A}; V_{DS} = 30 \text{ V}; T_{amb} = 25 \text{ }^\circ\text{C}$

Fig 14. Gate-source voltage as a function of gate charge; typical values

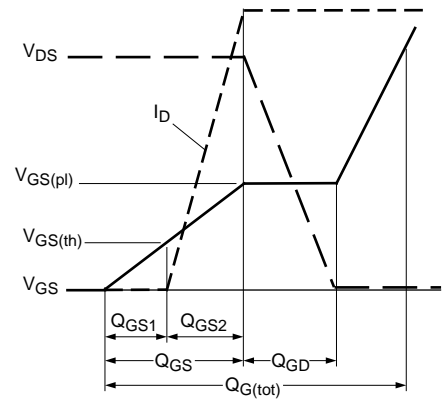
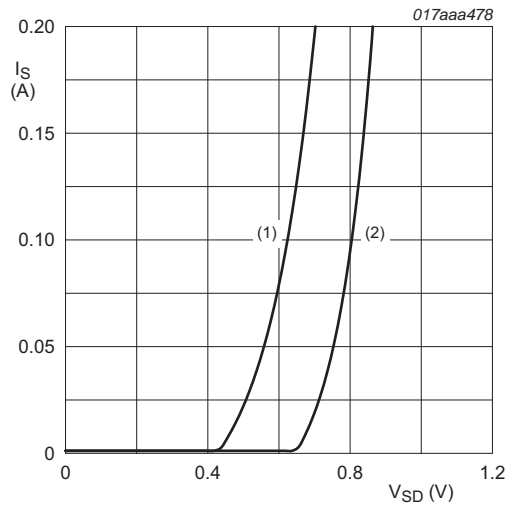


Fig 15. Gate charge waveform definitions



$V_{GS} = 0 \text{ V}$
 (1) $T_j = 150 \text{ }^\circ\text{C}$
 (2) $T_j = 25 \text{ }^\circ\text{C}$

Fig 16. Source current as a function of source-drain voltage; typical values

8. Test information



Fig 17. Duty cycle definition

9. Package outline

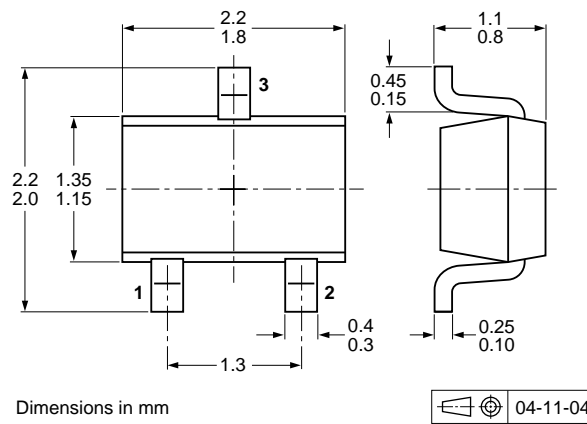


Fig 18. Package outline SOT323 (SC-70)

11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
NX7002AKW v.1	20120301	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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